

YG226S2 (5A)

(200V / 5A)

FAST RECOVERY DIODE

■ Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		250	V
Isolating voltage	V_{ISO}	Terminals-to-Case, AC.1min	1500	V
Average output current	I_o	Square wave, duty=1/2, $T_c=125^{\circ}C$	5	A
Surge current	I_{FSM}	Sine wave 10ms	70	A
Operating junction temperature	T_j		+150	$^{\circ}C$
Storage temperature	T_{stg}		-40 to +150	$^{\circ}C$

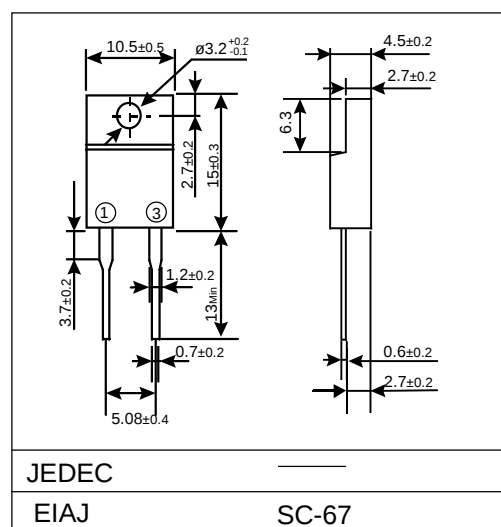
- Electrical characteristics (Ta=25°C Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=5A$	1.3	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	50	μA
Reverse recovery time	t_{rr}	$I_F=0.1A, I_R=0.1A$	0.4	μs
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5	$^{\circ}C/W$

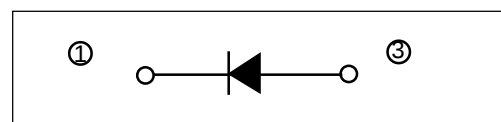
- Mechanical characteristics

Mounting torque	Recommended torque	0.3 to 0.5	N·m
Approximate weight		2.3	g

■ Outline drawings, mm

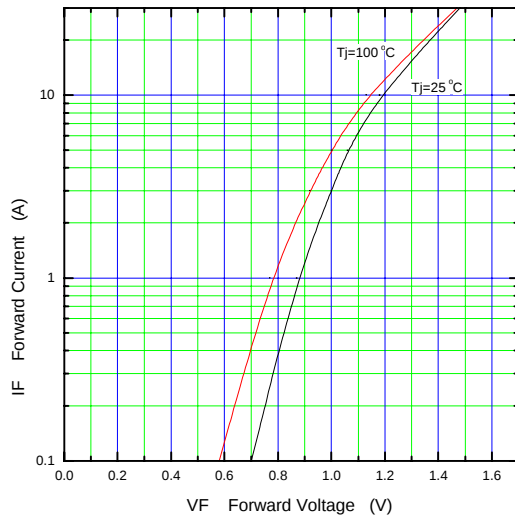


■ Connection Diagram

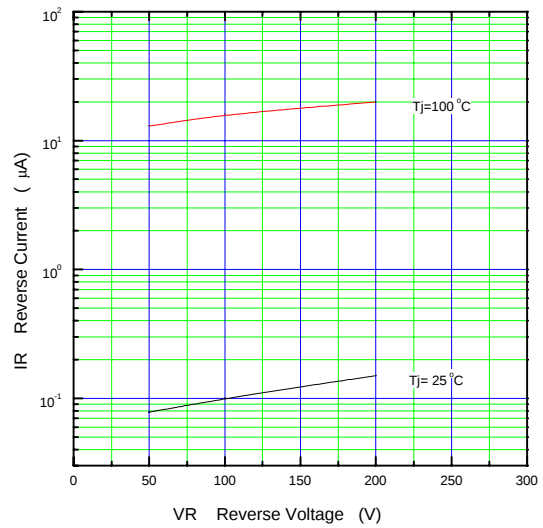


■ Characteristics

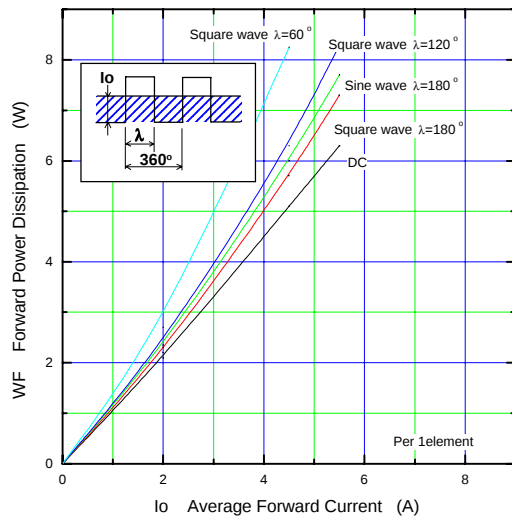
Forward Characteristic (typ.)



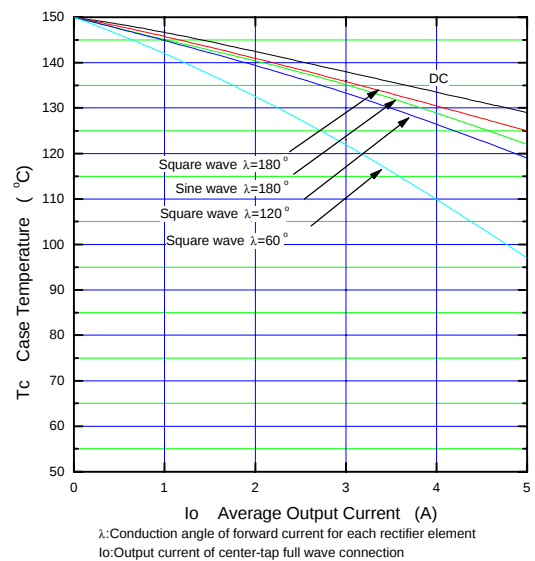
Reverse Characteristic (typ.)



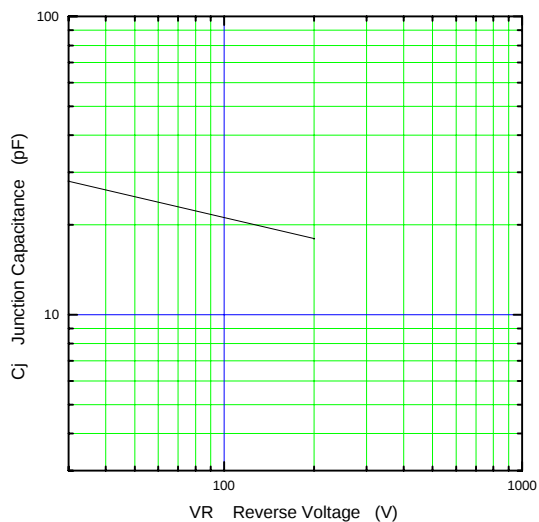
Forward Power Dissipation



Current Derating (I_o - T_c)



Junction Capacitance Characteristic (typ.)



Surge Capability

